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Transmission Electron Microscopy of Amorphisation and Recrystallisation of Silicon Nanowires under in situ Ion Irradiation

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Introduction

In the last decade, nanowires (NWs) have been the subject of intense scientific research and of particular interest are semiconductor NWs. Silicon NWs (Si) is an attractive material for the microelectronic industry due to its mechanical strength, abundance, cost, electrical properties, ease of wafer production and high-temperature performance. The quest to continually miniaturise Si-based microelectronics poses challenges as the limits of current technologies are reached. For example, at increasingly small dimensions issues such as leakage current and short channel effects become critical. Therefore, novel solutions are required with similar thermal, electrical, mechanical and optical properties whilst overcoming the shortcomings of bulk Si. Si NWs are one of the main candidates as they possess many of the same properties as bulk Si whilst offering solutions to many of the challenges faced by virtue of their geometry.

Ion irradiation is the main processing technique for Si-based devices. The current work is focused on understanding the underlying physics and mechanisms of amorphisation and recrystallisation of single-c得知 和 Si NWs under ion irradiation. The ion irradiation causes displacement of atoms and accumulation of damage resulting in the amorphisation of the NWs. However, the probability of the ions being implanted into the NW and the amount of damage they cause both vary as complicated functions of ion species, energy and NW diameter. Implantation of ions may perturb the amorphisation and recrystallisation processes under study. Therefore, the irradiation conditions must be designed to achieve maximum damage with the minimum amount of implanted ions. Monte Carlo calculations have been performed using the Stopping Range of ions in Matter codes [1] and these have been used to determine the optimum irradiation conditions, Fig 1.

Experimental

Preliminary experiments have been carried out using the microscope and ion accelerator facility at the University of Huddersfield. Irradiation of Si NWs with 40 keV Ar⁺ ions has been performed in situ with the JEOL JEM-2000FX transmission electron microscope (TEM) to induce amorphisation within the NWs. Commercially available polyimided Si Nanowires were used and have been irradiated at room temperature. The nanowires have been irradiated with a flux of 6.3×10⁸ ions cm⁻² s⁻¹.

Results and Discussion

Figs 2 and 3 represent a transition from crystalline Si (c-Si) to amorphous (a-Si) phase. Since c-Si has lower free energy than amorphous Si, there exists a tendency to recrystallise from a-Si to c-Si phase at elevated temperatures. It has been observed during the experiment that recrystallisation occurs at temperatures above 450°C.

Through design of the experiment geometry, it has been possible to use the specimen support to shadow part of the NWs from the ion beam and thus produce a crystalline amorphous (c-a) interface across the diameter of a NW. Further, by careful tuning of the ion energy to the NW diameter, it has been possible to create a buried c-a interface along the length of a NW. The irradiation causes the amorphisation of the 80 nm thick nanowire to be examined, with few dots in the diffraction pattern (DP) showing crystallites at the back side of nanowire due to low fluence of ion beam, Fig 2.

Upon thermal annealing, Si NWs undergo a recrystallisation process which has been found to cause either a return to a single-crystalline state similar to the pre-irradiated state or a polycrystalline state. Preliminary results suggest it is possible to control the recrystallisation via the engineering of the c-a interface. TEM images and diffraction patterns (DPs) are presented showing the amorphisation and recrystallisation processes in the crystalline, c-a interface and amorphous regions.

Further work will focus on the fundamental mechanisms behind the amorphisation and recrystallisation processes in Si NWs. It has been analysed from the DPs that the irradiated region of nanowire in Fig 3, mixed growth mechanism occurred following the recovery via layer by layer process called epitaxial growth and random nucleation growth (RNCG) for amorphised Si results into single crystal recovery.

Conclusions

Both the Solid Phase Epitaxial Growth (SPEG) and Random Nucleation Growth (RNCG) were seen in the amorphised Si nanowire during annealing experiment. Further experiments are needed to fully amorphise the NW at the calculated fluence of the ion beam with the diameter of Si NW and to quantitatively verify the recrystallisation phenomena occurring at the temperature of 450°C for Si NWs.

References


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